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Abstract: In this talk, we will present characterization of Terahertz (THz) wireless channel inside a desktop size metal enclosure as well as statistical modeling of this environment. Measurements indicate that both traveling wave and resonating modes exist inside the metal enclosure. Measurements for line-of-sight (LoS) propagation inside the empty metal enclosure show that the path loss significantly changes as a function of the transceiver's height. It is found that this variation is due the resonant modes contribution in the received power Furthermore, the path loss model that captures signal strength variation in a resonant cavity is proposed. Finally, it was shown that statistical model can capture propagation in metal enclosures. The results show a good agreement between the simulated and measured statistics.

Purpose: Information of IEEE 802.15 IG THz

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Measurements and Modeling of THz Chip-to-Chip Channels in Metal Enclosures

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July 2019



Motivation

Processor-Memory Wireless Interconnects in Metal Enclosures

Channel Measurements in Metal Enclosures

Channel Modeling of Propagation in Metal Enclosures

➢ Future Challenges

Internet of Everything



Challenges for IoT and Wearable Devices

- Sensing a complex environment -Innovative ways to sense and deliver information from the physical world to the cloud
- Connectivity- Variety of wireless networks needed
- Cloud is important IoT will require significant increase in data storage needs better rack-to-rack, device-to-device, and chipto-chip communication
- Security is vital Detecting and blocking malicious activity
- IoT is complex IoT application development needs to be easy for all developers, not just to experts
- Power is critical

Applications That Need THz Communication

Interconnects in Data Centers



Chip-to-Chip On Motherboard



Wearable Devices



Current Wireless Interconnects

- + antenna size/integration with chips
- +adding bandwidth without adding pins or fiber connectors to the chip package.
- limited bandwidth
- For example, a computer in a typical high performance cluster gets 56 Gbits/s
- Wireless communication at mm- Wave frequencies: WiGig uses 60 GHz frequency range to provide up to 7 Gbits/s using OFDM, 64- QAM, and sophisticated coding.
- Power hungry systems

THz Chip-to-Chip Wireless Communications in Metal Enclosures





- THz wireless communication on the motherboard, i.e. CPU-DIMM link, CPU-AGP link, etc.
- Channels are inside the desktop case which is mostly made out of metal.

[1] J. Fu, P. Juyal, and A. Zajic, "300 ghz channel characterization of chip-to-chip communication in metal enclosure," in 13th European Conference on Antennas and Propagation (EuCAP). IEEE, 2019, pp. 1–5.



TABLE I Measurement Parameters

parameter	Symbol	Value
Measurement points	N	801
Intermediate frequency bandwidth	$\Delta f_{ m IF}$	20 kHz
Average noise floor	$P_{\rm N}$	-90 dBm
Input signal power	$P_{\rm in}$	0 dBm
Start frequency	f_{start}	10 MHz
Stop frequency	$f_{ m stop}$	12 GHz
Bandwidth	В	11.99 GHz
Time domain resolution	Δt	0.067 ns
Maximum excess delay	$ au_{ m m}$	40 ns

300-320 GHz Measurement System



Dielectric resonator oscillator (25 GHz)

- THz Measurement Setup
 - ≻ N5224 VNA
 - Directional horn antennas with 3 dB beamwidths of 12° and the gain varies between 22 and 23 dBi.

Measurement Scenarios

- Line-of-sight inside a desktop size metal cavity
 - An aluminum cavity with the size of 30.5 cm × 30.5 cm × 10 cm.
 - Cavity was in between the Tx and Rx with antennas aligned horizontally.
 - Transceivers' height, h, varied from 0 cm to 6.6 cm with the step size of 0.6 cm.
 - Absorbers were used to eliminate reflections from the backsides of antenna





Measurement Scenarios

- RNLoS with DIMM as the Reflecting Surface
 - ➤ Tx and Rx were positioned perpendicular with each other.
 - A dual in-line memory modules (DIMM) was vertically put on the center of the bottom of the cavity along its diagonal.
 - ➤ Both flat and component sides of the DIMM were measured.
 - > Control experiments were performed in free space.





Measurement Scenarios



 LoS over FPGA board
 A FPGA board 15.2 x15.2 cm, the height of 1.5 cm.

- Located in the center of the bottom plate.
- EM wave travels through the FPGAs diagonals.
- Measured in air and in metal cavity

Measured Path Loss Inside Metal Cavity



- ➢ For *h* < 1.8 cm, measured path losses are lower than the Friis prediction (ground reflection).
- For 1.8 cm $\leq h \leq$ 6.6 cm, average of measured path losses are aligned with the Friis prediction.

Power Delay Profile in Metal Cavity



- Power delay profile
 - There are several clusters of peaks that arrive with the delay of 2.05 ns.
 - The difference between any two close paths is 61.5 cm (twice of the box's length).

RNLoS Path Loss Inside a Metal Cavity vs. Free Space

In Free Space In Metal Cavity 100 100 DIMM Component Side 95 ↔DIMM Flat Side 95 Friis 90 90 Loss [dB] Path Loss[dB] 85 85 80 80 Path 75 75 of a consistence of the consiste 70 70 -DIMM Component Side ↔DIMM Flat Side 65 65 --Without DIMM Calculated 60 60 3.02 3.04 3.06 3.08 3.1 3.12 3 3.04 3.06 3.08 3.1 3 3.02 3.12 ×10¹¹ $imes 10^{11}$ Frequency [Hz] Frequency[Hz]

RNLoS PDP Inside a Metal Cavity

- Power delay profile
 Flat side of the DIMM
 Two arriving peaks with excess delay of 2.05 ns and 4.09 ns.
 - Component side of the DIMM
 - Two arriving peaks with excess delay of 1.17 ns and 2.05 ns.



RNLoS Path Loss Over FPGA

➢ In Free Space

In Metal Cavity



RNLoS PDP Over FPGA



Path Loss Model



$$(PL^T)_{dB} = \left(\overline{\widetilde{PL}}\right)_{dB} + 10\log_{10}(|E|^2)^{-1}$$

- $\succ (PL^T)_{dB}: \text{ theoretical path } loss.$
 - $\succ \overline{\widetilde{PL}}$: mean path loss of traveling wave.
 - 10 log₁₀(|E|²)⁻¹: received power variation contributed by resonant modes



$$(PL^T)_{dB} = \left(\overline{\widetilde{PL}}\right)_{dB} + 10\log_{10}(|E|^2)^{-1}$$

• Mean path loss

•
$$\overline{\widetilde{PL}} = \frac{1}{\Delta f} \int_{\Delta f} \left(\frac{4\pi df}{c} \right) df$$

- d = D = 30.5 cm.
- c is the speed of light.
- $\Delta f = 12$ GHz.

Path Loss Model

$$(PL^T)_{dB} = \left(\overline{\widetilde{PL}}\right)_{dB} + 10\log_{10}(|E|^2)^{-1}$$

Power contributed by resonant modes

 \succ The transverse components of the electric field of TE mode.

$$|E|^{2} = |E_{x}|^{2} + |E_{y}|^{2}.$$

$$E_{x} = \frac{-j\omega_{mnp}\mu k_{y}H_{0}}{k_{mnp}^{2}-k_{z}^{2}}\cos\frac{m\pi y}{a}\sin\frac{n\pi y}{b}\sin\frac{p\pi z}{c}.$$

$$E_{y} = \frac{j\omega_{mnp}\mu k_{x}H_{0}}{k_{mnp}^{2}-k_{z}^{2}}\sin\frac{m\pi x}{a}\cos\frac{n\pi y}{b}\sin\frac{p\pi z}{c}.$$

$$k_{mnp}^{2} = \left(\frac{m\pi}{a}\right)^{2} + \left(\frac{n\pi}{b}\right)^{2} + \left(\frac{p\pi}{c}\right)^{2}.$$

$$f_{mnp} = \frac{1}{2\sqrt{\mu\epsilon}}\sqrt{\left(\frac{m}{a}\right)^{2} + \left(\frac{n}{b}\right)^{2} + \left(\frac{p}{c}\right)^{2}}.$$

$$(a)$$

$$(b)$$

Path Loss Model and Comparison With Measurements



- The first 8 TE modes dominate the resonate modes inside the cavity with curve-fitting.
- The coefficients of these modes are

$$A_{1} = 0.441,$$

$$B_{1} = -0.173,$$

$$A_{2} = -0.583,$$

$$B_{2} = 0.060,$$

$$A_{3} = 0.757,$$

$$B_{3} = -0.056,$$

$$A_{4} = -0.254,$$

$$A_{4} = -0.254,$$

$$A_{5} = 0.274,$$

$$B_{5} = -0.112,$$

$$A_{6} = 0.128,$$

$$B_{6} = 0.394,$$

$$A_{7} = 0.968,$$

$$B_{7} = 0.892,$$

$$A_{8} = 0.269,$$

$$B_{8} = 0.323.$$

Including Antenna Misalignment

$$(PL)_{dB} = \overline{(PL^t)}_{dB} + 10\log_{10}(|E|^2)^{-1} + 10\log_{10}\left(|g(\alpha_t)g(\alpha_r)|^2\right)^{-1}$$

- The loss due to the misalignment between the Tx and Rx.
- $g(\alpha)$ represents the radiation pattern of the diagonal horn antenna.

•
$$g(\alpha) = \begin{cases} X + Y \cos(Z\alpha) & -\theta \le \alpha \le \theta \\ c & otherwise \end{cases}$$

• θ is half beamwidth of the diagonal horn antenna.

Path Loss Model

- Verification measurements
 Similar measurement setup with the inbox LoS measurements.
 - ➢ Rx height, h_r, varies from 0cm to 6.6cm with Tx height, h_t, being fixed at 2.4cm.
 - A good agreement can be found between the measured and calculated path loss.





Channel Modeling

- Both traveling wave and resonant modes exist inside the metal cavity.
- Traveling wave inside the metal enclosure is likely to excite the cavity.
- Transceiver sidewalls of the cavity can be treated both as consecutive scatters and the sources of EM waves.
- The generated EM waves are considered and modeled as multi-bounced (MB) rays.
- Two dominate propagation mechanisms:
 - LoS: signal travels directly from Tx to Rx.
- MB: signal bounces back and forth between the transceiver side

Geometrical Model for LoS Propagation in Metal Cavity



Model Parameters

- D, a: length and height of the cavity.
- \succ h: height of both Tx and Rx.
- M,Q: scatters uniformly distributed on Tx and Rx sidewalls.
- \$\theta_T, \theta_R\$: half-beamwidth of Tx and Rx antenna.
 \$S_T^m, S_R^q\$: the mth and qth scatter on the Tx and Rx sidewall.
 \$\alpha_T^m, \alpha_R^q\$: the angle of departure and arrival.
 \$\alpha_T^m = -\theta_T + \frac{2(m-1)}{M-1}\theta_T, \$\alpha_T^m = -\theta_R + \frac{2(m-1)}{M-1}\theta_T.
 \$\epsilon_T^m, \epsilon_R^q, \epsilon_S^m^q\$: the distances of Tx \$S_T^m, S_R^q\$ Rx, and \$S_T^m\$ \$S_R^q\$.

Channel Model for LoS Propagation in Metal Cavity

$$h(\tau) = h^{LoS}(\tau) + h^{MB}(\tau).$$

$$h^{LoS}(\tau) = \sqrt{\frac{\kappa}{\kappa+1}} A_{LoS} e^{j\phi_{LoS}} \delta(\tau - \tau_{LoS}).$$

- ➢ K is the Ricean factor.
- > A_{LoS} , $e^{j\phi_{los}}$, and τ_{LoS} represent LoS amplitude, phase, and time delay.

➤
$$A_{LoS} = \sqrt{\frac{P_t G_t G_r}{PL_{loS}}}$$
, where P_t , G_t , G_r , and PL represent transmit power, transmit gain, receive gain, and path loss.

Channel Model for LoS Propagation in Metal Cavity

$$h^{MB}(\tau) = \sqrt{\frac{1}{K+1}} \cdot \frac{1}{\sqrt{LMQ}} \sum_{l=1}^{L} \sum_{m=1}^{M} \sum_{q=1}^{Q} A_{lmq} e^{j\phi_{lmq}} \delta(\tau - \tau_{lmq})$$

$$L \text{ is the number of later arriving rays.}$$

$$A_{lmq}, \phi_{lmq}, \text{ and } \tau_{lmq} \text{ represent the amplitude, phase, and time delay of multipath components.}$$

$$A_{lmq} = \sqrt{\frac{P_t G_t G_T}{PL_{lmq}}} f(\alpha_T^m) f(\alpha_R^q), \text{ where } f(\psi) = X + Y\cos(Z\psi).$$

$$(PL)_{dB} = \left(\overline{PL}\right)_{dB} + 10\log_{10}(|E|^2)^{-1}.$$

$$\overline{PL} = \frac{1}{\Delta f} \int_{\Delta f} \left(\frac{4\pi df}{c}\right)^2 df, |E|^2 = \left|\sum_{n=1}^{N} E_{yn}\right|^2 + \left|\sum_{n=1}^{N} E_{xn}\right|^2.$$

$$For \text{ Los: } d = D.$$

$$For MB: d = D_L = \left(\epsilon_T^m + \epsilon_R^q + (2L-1)\epsilon_{ang}\right), \epsilon_{avg} = \frac{1}{MQ} \sum_{m=1}^{M} \sum_{q=1}^{Q} \epsilon_S^{mq}.$$

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Comparison Between Modeled and Measured PDPs

- The size of the metal cavity is 30.5 cm×30.5 cm×9.6 cm.
- > The simulated PDPs are obtained with:
- L=5, M=Q=45, K=17.36 and 33.04 for h=2.4 cm and 1.2 cm.
- > Parameters for $f(\psi)$ are X=0.54, Y=0.45, Z=11.15.







h=1.2 cm

*Summary

- Both traveling wave and resonate modes exist in the metal enclosure.
- The first 8 TE modes dominate the resonate modes in the metal cavity
- > For the RNLoS propagation, traveling wave dominates channel.
- Also resonate modes lead to the stronger fluctuation of path losses over the frequency band.
- Statistical channel modeling can be used to represent resonant modes in the metal cavity

Research Challenges

Cost and energy efficient transceivers

Antenna design for efficient communication over small distances

- Channel modeling at THz frequencies
- Low-complexity modulation and coding schemes



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THANK YOU

Questions?